

N-channel 600 V, 0.14 Ω typ., 20 A MDmesh™ M2 Power MOSFETs in TO-220 and TO-247 packages

Datasheet - production data

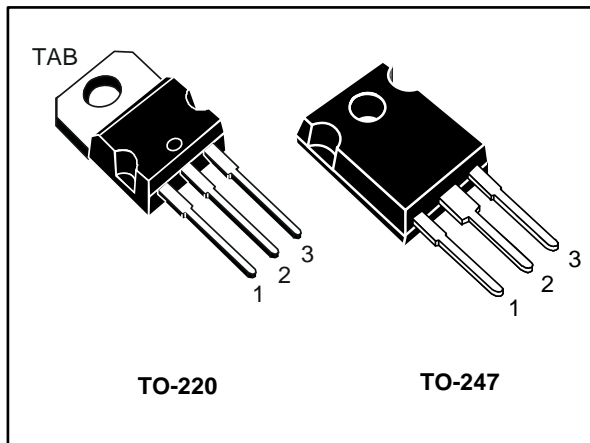
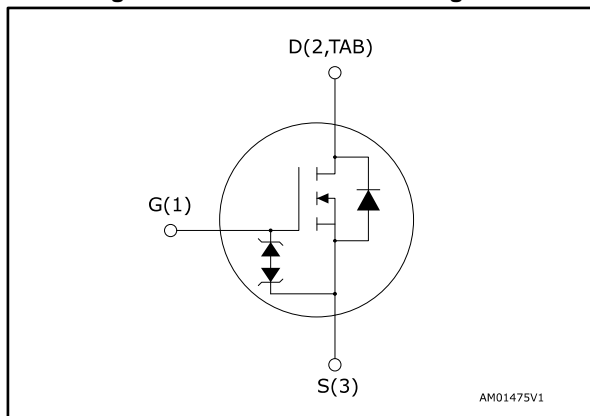


Figure 1: Internal schematic diagram



Features

Order code	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STP26N60M2	650 V	0.165 Ω	20 A	169 W
STW26N60M2				

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STP26N60M2	26N60M2	TO-220	Tube
STW26N60M2		TO-247	

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves).....	6
3	Test circuits	9
4	Package information	10
	4.1 TO-220 type A package information.....	11
	4.2 TO-247 package information.....	13
5	Revision history	15

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at $T_{case} = 25\text{ °C}$	20	A
	Drain current (continuous) at $T_{case} = 100\text{ °C}$	13	
$I_{DM}^{(1)}$	Drain current (pulsed)	80	A
P_{TOT}	Total dissipation at $T_{case} = 25\text{ °C}$	169	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		

Notes:

(1) Pulse width is limited by safe operating area.

(2) $I_{SD} \leq 20\text{ A}$, $di/dt=400\text{ A}/\mu\text{s}$; $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.

(3) $V_{DS} \leq 480\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value		Unit
		TO-220	TO-247	
$R_{thj-case}$	Thermal resistance junction-case	0.74		°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient	62.5	50	

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	3.8	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	250	mJ

Notes:

(1) Pulse width limited by T_{jmax} .

(2) starting $T_j = 25\text{ °C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$ unless otherwise specified)

Table 5: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$			1	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$, $T_{\text{case}} = 125\text{ °C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 25\text{ V}$			± 10	μA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 10\text{ A}$		0.14	0.165	Ω

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ISS}	Input capacitance	$V_{\text{DS}} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	1360	-	pF
C_{OSS}	Output capacitance		-	88	-	
C_{RSS}	Reverse transfer capacitance		-	2	-	
$C_{\text{OSS eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }480\text{ V}$, $V_{\text{GS}} = 0\text{ V}$	-	124	-	pF
R_{G}	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_{\text{D}} = 0\text{ A}$	-	4	-	Ω
Q_{g}	Total gate charge	$V_{\text{DD}} = 480\text{ V}$, $I_{\text{D}} = 20\text{ A}$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 17: "Test circuit for gate charge behavior")	-	34	-	nC
Q_{gs}	Gate-source charge		-	5.6	-	
Q_{gd}	Gate-drain charge		-	16.3	-	

Notes:

⁽¹⁾ $C_{\text{OSS eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{OSS} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$, $I_{\text{D}} = 10\text{ A}$, $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 16: "Test circuit for resistive load switching times" and Figure 21: "Switching time waveform")	-	20.2	-	ns
t_{r}	Rise time		-	8	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	66	-	
t_{f}	Fall time		-	10	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		20	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		80	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 20\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 20\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 18 : "Test circuit for inductive load switching and diode recovery times")	-	360		ns
Q_{rr}	Reverse recovery charge		-	5		μC
I_{RRM}	Reverse recovery current		-	27		A
t_{rr}	Reverse recovery time	$I_{SD} = 20\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 18 : "Test circuit for inductive load switching and diode recovery times")	-	556		ns
Q_{rr}	Reverse recovery charge		-	8		μC
I_{RRM}	Reverse recovery current		-	29		A

Notes:

- (1) Pulse width is limited by safe operating area.
(2) Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

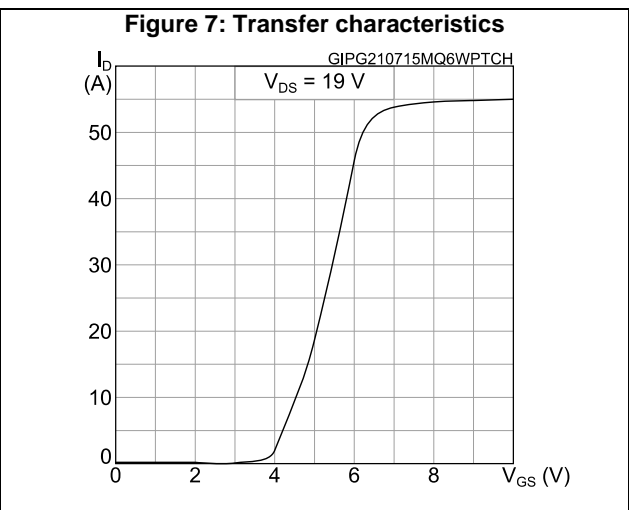
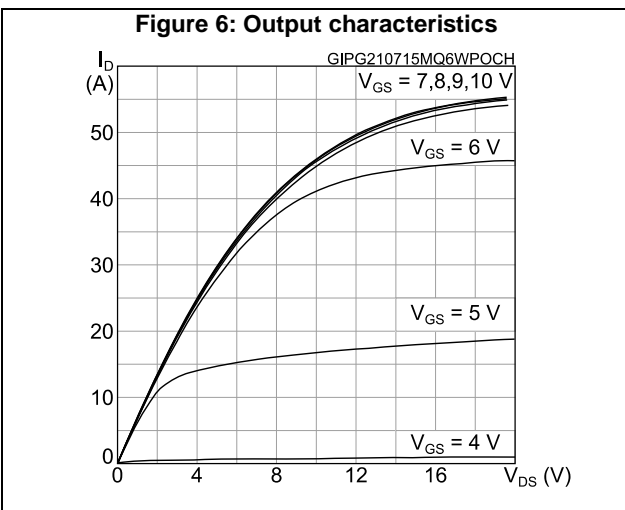
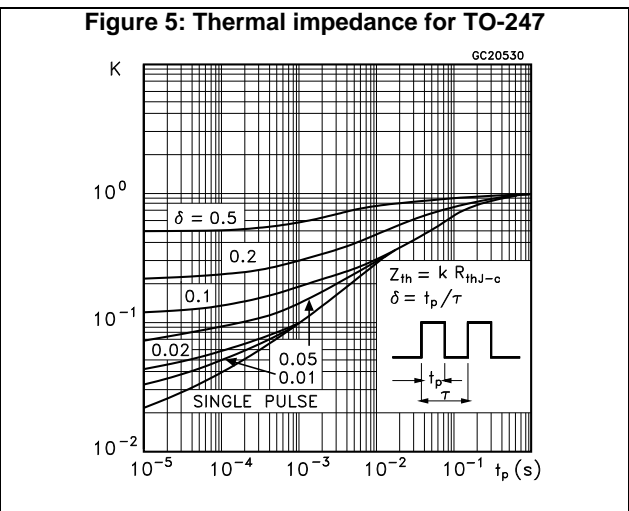
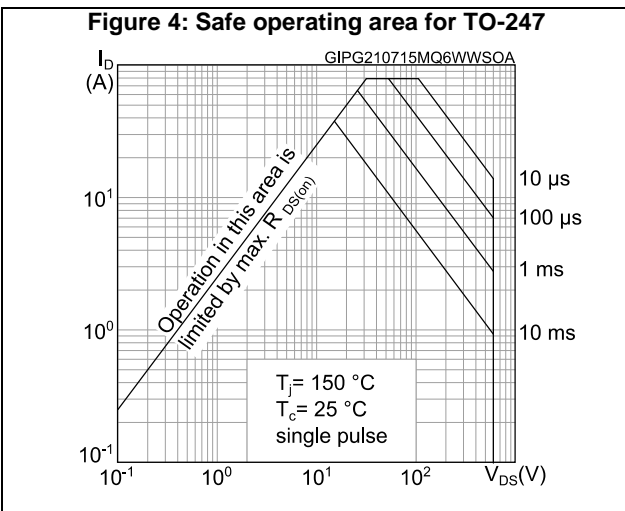
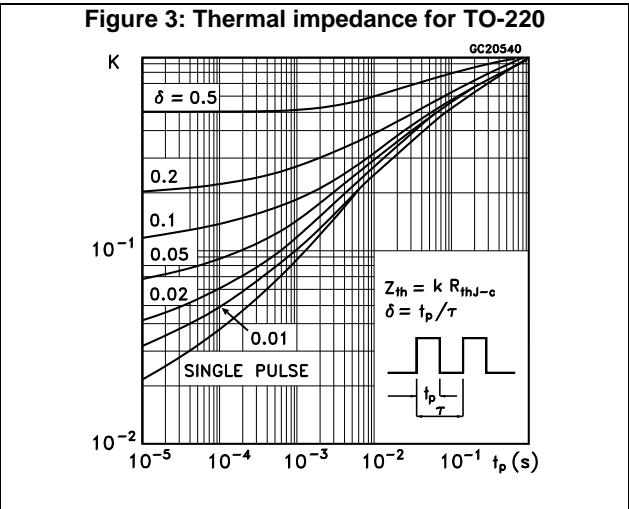
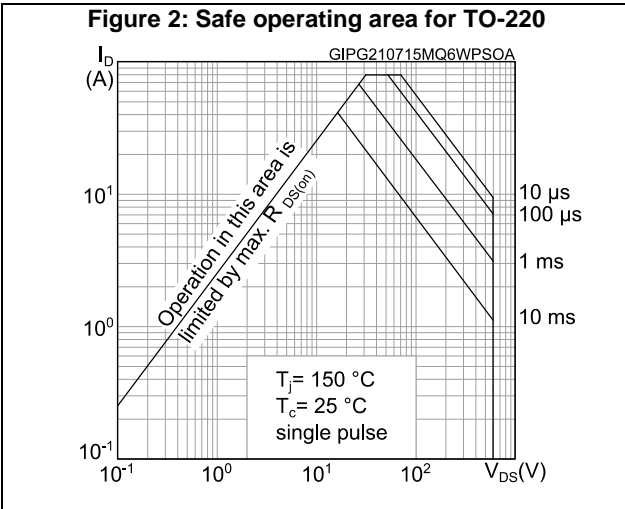


Figure 8: Gate charge vs gate-source voltage

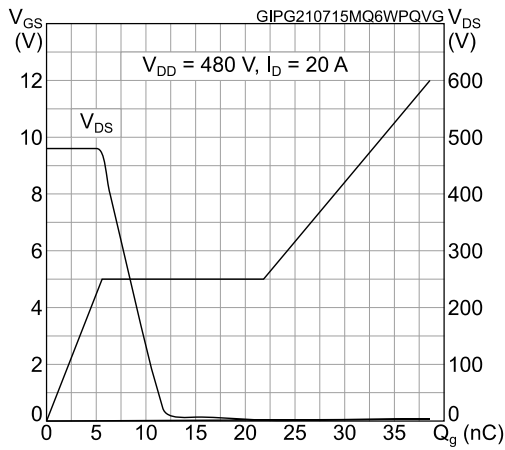


Figure 9: Static drain-source on-resistance

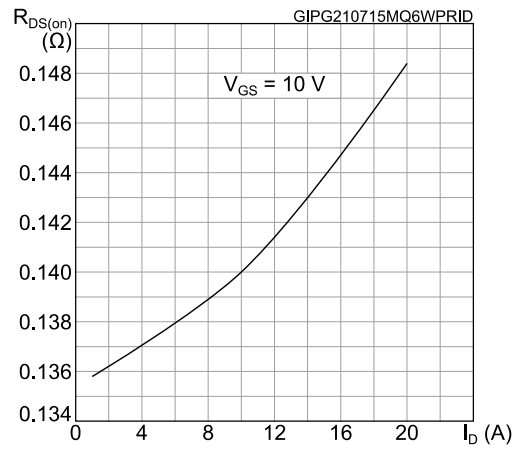


Figure 10: Capacitance variations

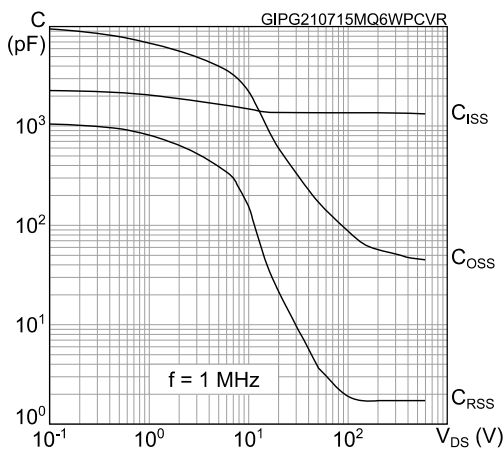


Figure 11: Normalized gate threshold voltage vs temperature

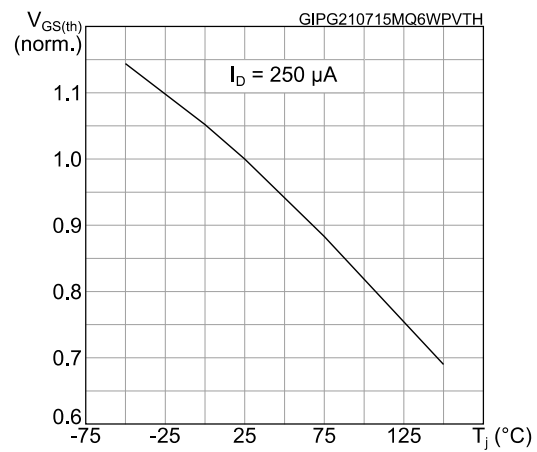


Figure 12: Normalized on-resistance vs temperature

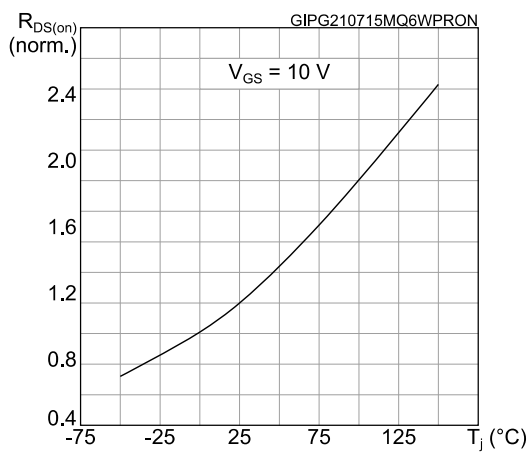


Figure 13: Normalized V(BR)DSS vs temperature

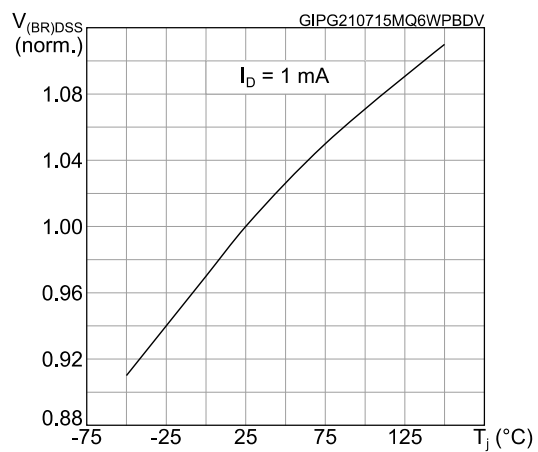


Figure 14: Output capacitance stored energy

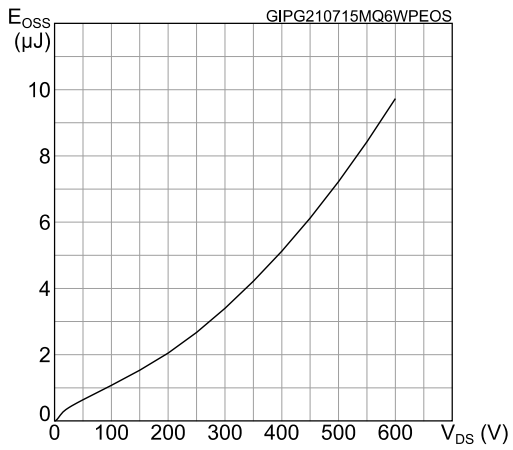
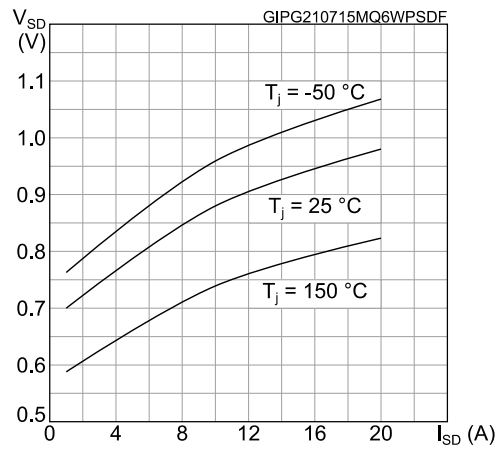


Figure 15: Source-drain diode forward characteristics



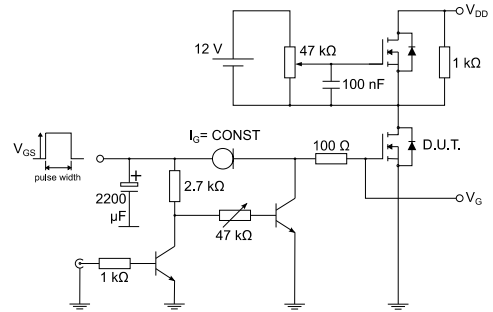
3 Test circuits

Figure 16: Test circuit for resistive load switching times



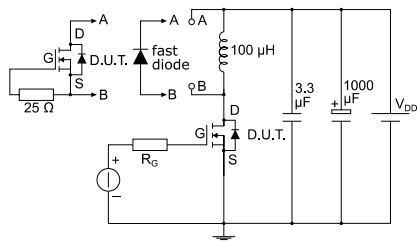
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Figure 17: Test circuit for gate charge behavior



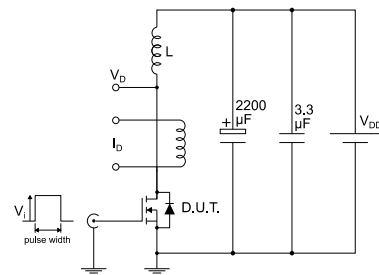
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Figure 18: Test circuit for inductive load switching and diode recovery times



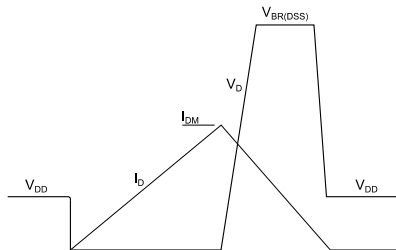
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Figure 19: Unclamped inductive load test circuit



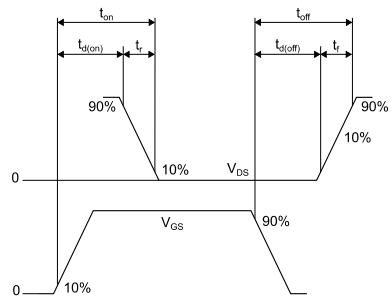
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Figure 20: Unclamped inductive waveform



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Figure 21: Switching time waveform



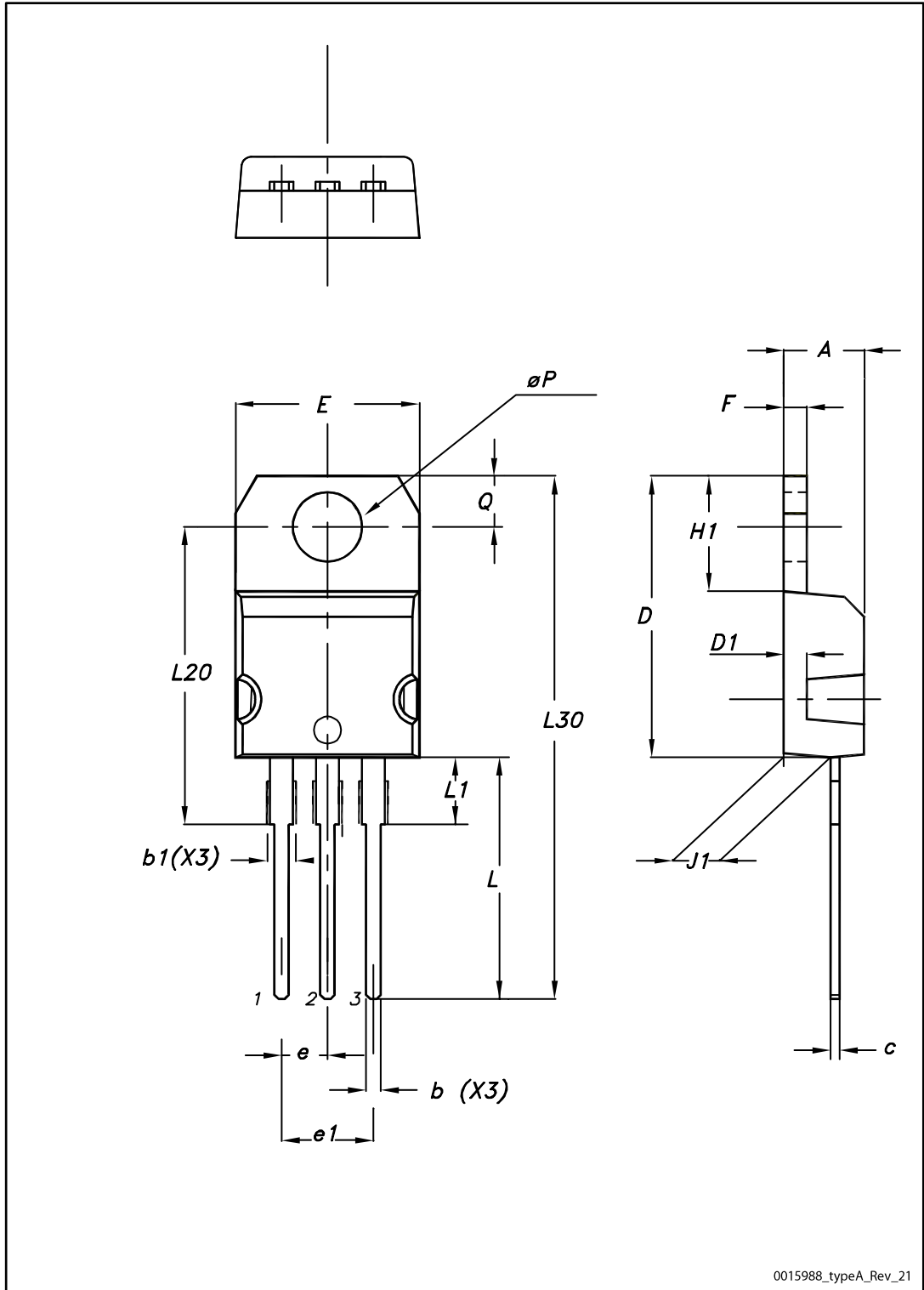
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-220 type A package information

Figure 22: TO-220 type A package outline



0015988_typeA_Rev_21

Table 9: TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.2 TO-247 package information

Figure 23: TO-247 package outline

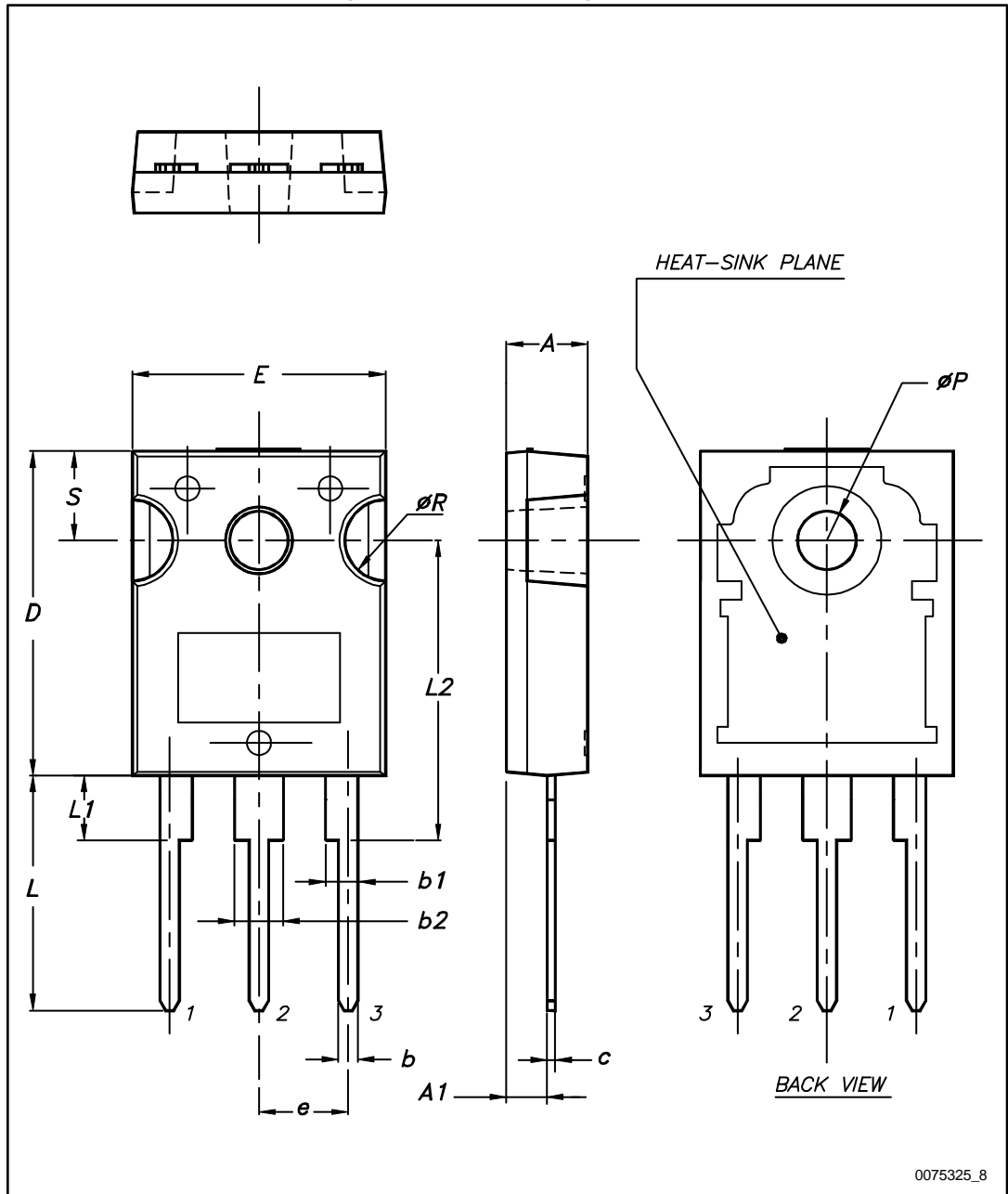


Table 10: TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

5 Revision history

Table 11: Document revision history

Date	Revision	Changes
03-Aug-2015	1	First release.
08-Mar-2017	2	Updated <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 3: "Thermal data"</i> and <i>Figure 10: "Capacitance variations"</i> . Minor text changes.

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